## NSN 5961-01-105-4621

**Inclosure Material:**Ceramic all transistor

**Unit Of Measure:** 

Semiconductor Device Set - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-105-4621

Overall Length:
0.980 inches all transistor
Overall Height:
0.300 inches all transistor
Overall Width:
0.850 inches all transistor
Mounting Facility Quantity:
2 all transistor
Internal Configuration:
Junction contact all transistor
Internal Junction Configuration:
Npn all transistor
Component Function Relationship:
Matched
Component Name And Quantity:
4 transistor
Mounting Method:
Unthreaded hole all transistor
Field Force Effect Type:
Electrostatic charge
Semiconductor Material:
Silicon all transistor
Voltage Rating In Volts Per Characteristic:
65.0 collector to base voltage/static/emitter open all transistor and 33.0 collector to emitter voltage/static/base open all transistor and 65.0
collector to emitter voltage, dc with base short-circuited to emitter all transistor and 4.0 emitter to base voltage, static, collector open all
transistor
Current Rating Per Characteristic:
3.00 amperes source cutoff current all transistor and 20.00 amperes source cutoff current all transistor
Power Rating Per Characteristic:
270.0 watts small-signal input power, common-collector absolute all transistor
Maximum Operating Tempurature Per Measurement Point:
200.0 degrees celsius junction all transistor
Special Features:
Case contains beryllium oxide - handle and dispose iaw hazmat procedures
Test Data Document:
13499-352-1108 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.;
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
6 ribbon all transistor
Shelf Life:
N/a

## NSN 5961-01-105-4621

Semiconductor Device Set - Page 2 of 2



Demilitarization:

No

Fiig:

A110a0